

Pablo O Vaccaro

List of Publications by Year in descending order

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116
papers

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citations

394286

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119
all docs

119
docs citations

119
times ranked

825
citing authors

#	ARTICLE	IF	CITATIONS
1	Localized thinning for strain concentration in suspended germanium membranes and optical method for precise thickness measurement. AIP Advances, 2018, 8, 115131.	0.6	3
2	Thermal transport in epitaxial Si _{1-x} Ge _x alloy nanowires with varying composition and morphology. Nanotechnology, 2017, 28, 505704.	1.3	9
3	Spectroscopic imaging ellipsometry of self-assembled SiGe/Si nanostructures. Applied Surface Science, 2017, 421, 547-552.	3.1	1
4	Growth and Characterization of Epitaxial In-plane SiGe Alloy Nanowires. Materials Today: Proceedings, 2015, 2, 548-556.	0.9	4
5	Composition and Strain Imaging of Epitaxial In-Plane SiGe Alloy Nanowires by Micro-Raman Spectroscopy. Journal of Physical Chemistry C, 2015, 119, 22154-22163.	1.5	6
6	Electric Field Induced Carrier Sweep-Out in Tandem InGaN Multi-Quantum-Well Self-Pulsating Laser Diodes. Japanese Journal of Applied Physics, 2011, 50, 020209.	0.8	4
7	Electric Field Induced Carrier Sweep-Out in Tandem InGaN Multi-Quantum-Well Self-Pulsating Laser Diodes. Japanese Journal of Applied Physics, 2011, 50, 020209.	0.8	0
8	Pressure dependence of the electronic structure of a [311] piezoelectric $Ga_{0.85}Mn_{0.15}$. Physical Review B, 2010, 82, .	1.1	1
9	Highly reliable 500 mW laser diodes with epitaxially grown AlON coating for high-density optical storage. Applied Physics Letters, 2009, 95, .	1.5	22
10	Blue Laser Diodes Fabricated on m -Plane GaN Substrates. Applied Physics Express, 2008, 1, 011104.	1.1	48
11	Acoustic phonon Raman scattering induced by a built-in electric field. Physical Review B, 2008, 77, .	1.1	7
12	Selective optical generation of a coherent acoustic nanocavity mode. AIP Conference Proceedings, 2007, , .	0.3	0
13	Confined optical phonons in piezoelectric [311] GaInAs/AlAs superlattices probed by Raman scattering. Journal of Physics: Conference Series, 2007, 92, 012067.	0.3	0
14	Strain profile of the wall of semiconductor microtubes: A micro-Raman study. Physica Status Solidi (B): Basic Research, 2007, 244, 380-385.	0.7	0
15	Selective Optical Generation of Coherent Acoustic Nanocavity Modes. Physical Review Letters, 2007, 98, 265501.	2.9	56
16	Nonradiative centers in InAs quantum dots revealed by two-wavelength excited photoluminescence. Physica B: Condensed Matter, 2006, 376-377, 849-852.	1.3	6
17	Effect of material anisotropy on the self-positioning of nanostructures. Nanotechnology, 2006, 17, 1128-1133.	1.3	8
18	Strain Reduction and Long Wavelength Emission from InAs/GaAs Quantum Dots by Using Growth Interruption in Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2430-2432.	0.8	0

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19	Probing residual strain in InGaAs [∞] GaAs micro-origami tubes by micro-Raman spectroscopy. Journal of Applied Physics, 2006, 99, 063512.	1.1	23
20	Self-assembled GaAs micromirrors monolithically integrated with LEDs. , 2005, , .		3
21	Optimization of InAs quantum dots formation on (311)A substrate. Journal of Crystal Growth, 2005, 275, e2257-e2261.	0.7	2
22	Piezoelectric semiconductor acoustic cavities. Physical Review B, 2005, 72, .	1.1	10
23	Interdiffusion of Indium in piezoelectric InGaAs [∞] GaAs quantum wells grown by molecular beam epitaxy on (11n) substrates. Journal of Applied Physics, 2004, 96, 3702-3708.	1.1	9
24	Fabrication and current-drive of SiGe [∞] Si [∞] Micro-origami [∞] ™ epitaxial MEMS device on SOI substrate. Electronics Letters, 2004, 40, 1333.	0.5	9
25	Uniaxial-strain-induced transition from type-II to type-I band configuration of quantum well microtubes. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 732-736.	1.3	16
26	Physics and characteristics of a lateral p [∞] n junction tunneling transistor. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 867-871.	1.3	3
27	Si doped p- and n-type Al _x Ga _{1-x} As epilayers for high density lateral-junction LED arrays on (311)A patterned substrate. Solid-State Electronics, 2004, 48, 1791-1794.	0.8	0
28	Optical and transport studies in coupled InAs quantum dots embedded in GaAs. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 317-321.	1.3	0
29	Lateral junctions for high-density integration of optoelectronic devices. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 324-328.	1.3	0
30	Self-assembling GaAs mirror with electrostatic actuation using micro-origami. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 24, 78-81.	1.3	11
31	Characterization of GaAs-based micro-origami mirrors by optical actuation. Microelectronic Engineering, 2004, 73-74, 429-434.	1.1	21
32	Morphological dependence of lasing modes in two-dimensional quasi-stadium laser diodes. Journal of the Optical Society of America B: Optical Physics, 2004, 21, 935.	0.9	35
33	Novel LEDs using unique lateral p-n junctions on GaAs (311)A patterned substrates. , 2004, 5366, 212.		0
34	Inter-dot electron transport in coupled InAs quantum dots under a magnetic field. Semiconductor Science and Technology, 2004, 19, S54-S55.	1.0	2
35	High-density light-emitting diodes using a lateral p-n junction on patterned (311)A GaAs substrates. IEICE Electronics Express, 2004, 1, 86-91.	0.3	0
36	Lateral p [∞] n junctions for high-density LED arrays. Microelectronics Journal, 2003, 34, 355-357.	1.1	2

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37	Valley-fold and mountain-fold in the micro-origami technique. <i>Microelectronics Journal</i> , 2003, 34, 447-449.	1.1	34
38	Photoluminescence property of uniaxial strained GaAs/AlGaAs quantum wells contained in a micro-tube. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 17, 391-392.	1.3	3
39	InAs quantum dots on GaAs substrates with InGaAs strain reducing layer for long wavelength emission. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1193-1196.	0.8	8
40	Quasi-stadium laser diodes with an unstable resonator condition. <i>Optics Letters</i> , 2003, 28, 408.	1.7	12
41	Quantum-well microtube constructed from a freestanding thin quantum-well layer. <i>Applied Physics Letters</i> , 2003, 83, 1017-1019.	1.5	34
42	Optical actuation of micromirrors fabricated by the micro-origami technique. <i>Applied Physics Letters</i> , 2003, 83, 3647-3649.	1.5	49
43	Lasing on scar modes in fully chaotic microcavities. <i>Physical Review E</i> , 2003, 67, 015207.	0.8	69
44	Lasing characteristics and modal gain of a lateral-junction InGaAs/GaAs edge-emitting laser diode grown on a patterned GaAs (311) A-oriented substrate. <i>Applied Physics Letters</i> , 2003, 82, 2951-2953.	1.5	3
45	Self-Assembly of Microstage Using Micro-Origami Technique on GaAs. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 4079-4083.	0.8	27
46	SiGe/Si microtubes fabricated on a silicon-on-insulator substrate. <i>Journal Physics D: Applied Physics</i> , 2003, 36, L67-L69.	1.3	16
47	Array of Micromachined Components Fabricated Using "Micro-Origami" Method. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 4024-4026.	0.8	14
48	Device model for three-terminal lateral p-n junction quantum well lasers. , 2003, , .		0
49	Photoluminescence from High Γ -Electron Subbands and Intersubband Electroluminescence Using $X\alpha$ Carrier Injection in a Simple GaAs/AlAs Superlattice. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5073-5077.	0.8	1
50	Excitation of plasma oscillations and terahertz photomixing in high-electron mobility transistor. , 2002, , .		0
51	Ring and axis mode lasing in quasi-stadium laser diodes with concentric end mirrors. <i>Optics Letters</i> , 2002, 27, 1430.	1.7	26
52	Plasma mechanism of terahertz photomixing in high-electron mobility transistor under interband photoexcitation. <i>Journal of Applied Physics</i> , 2002, 92, 5756-5760.	1.1	60
53	Performance analysis of lateral p-n junction laser-transistor. <i>Journal of Applied Physics</i> , 2002, 92, 4459-4464.	1.1	4
54	Photoluminescence of GaAs/AlGaAs micro-tubes containing uniaxially strained quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 313-316.	1.3	35

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55	Strain-driven self-positioning of micromachined structures. Applied Physics Letters, 2001, 78, 2852-2854.	1.5	145
56	High-frequency performance of lateral p-n junction photodiodes. IEEE Journal of Quantum Electronics, 2001, 37, 830-836.	1.0	9
57	Steady-state characteristics of lateral p-n junction vertical-cavity surface-emitting lasers. Journal of Applied Physics, 2001, 90, 2654-2659.	1.1	2
58	Intersubband electroluminescence using X ⁻ carrier injection in a GaAs/AlAs double-quantum-well superlattice. Springer Proceedings in Physics, 2001, , 729-730.	0.1	0
59	High-resolution X-ray diffraction study of AlAs/Al _{0.5} Ga _{0.5} As/GaAs quantum well structures grown by molecular beam epitaxy on (111)A GaAs. Journal of Crystal Growth, 2000, 213, 214-220.	0.7	0
60	Optical properties of self-assembled InAs quantum dots grown on GaAs(211)A substrate. Thin Solid Films, 2000, 380, 97-100.	0.8	2
61	Possibility of a quasi-liquid layer of As on GaAs substrate grown by MBE as observed by enhancement of Ga desorption at high As pressure. Applied Surface Science, 2000, 159-160, 301-307.	3.1	10
62	Population inversion between subbands in simple periodical GaAs/AlAs superlattices. IEE Proceedings: Optoelectronics, 2000, 147, 225-228.	0.8	1
63	Intersubband electroluminescence using X ⁻ carrier injection in a GaAs/AlAs superlattice. Applied Physics Letters, 2000, 77, 848-850.	1.5	3
64	Local degradation of selectively oxidized AlGaAs/AlAs distributed Bragg reflectors in lateral-injection vertical-cavity surface-emitting lasers. Applied Physics Letters, 2000, 77, 3905-3907.	1.5	1
65	Optoelectronic devices based on lateral p-n junctions fabricated by molecular-beam epitaxy growth of silicon-doped GaAs on patterned (311)A-oriented substrates. IEEE Journal of Quantum Electronics, 2000, 36, 849-857.	1.0	17
66	Electroluminescence in Undoped GaAs/AlAs Superlattice due to Avalanche Breakdown. Japanese Journal of Applied Physics, 1999, 38, 2577-2579.	0.8	8
67	Time resolved magneto-optical spectroscopy on InGaAs nanostructures grown on (311)A and (100)-oriented substrates. Applied Physics Letters, 1999, 74, 676-678.	1.5	6
68	Lateral-junction vertical-cavity surface-emitting laser grown by molecular-beam epitaxy on a GaAs (311)A-oriented substrate. Applied Physics Letters, 1999, 74, 3854-3856.	1.5	22
69	Arsenic vapor pressure dependence of surface morphology and silicon doping in molecular beam epitaxial grown GaAs (111)A (n=1-4) substrates. Microelectronics Journal, 1999, 30, 471-476.	1.1	21
70	AlAs oxidation process in GaAs/AlGaAs/AlAs heterostructures grown by molecular beam epitaxy on GaAs (111)A substrates. Microelectronics Journal, 1999, 30, 387-391.	1.1	10
71	Optical transitions of Al _{0.35} Ga _{0.65} As/GaAs asymmetric double quantum wells grown on GaAs(111)A (n=4) substrates. Microelectronics Journal, 1999, 30, 433-437.	1.1	6
72	Lateral wet oxidation of AlAs layer in GaAs/AlAs heterostructures grown by MBE on GaAs (111)A substrates. Journal of Crystal Growth, 1999, 198-199, 1136-1140.	0.7	4

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73	MBE growth of AlGaAs/GaAs heterostructure and silicon doping on GaAs(111)A ($n=1\text{--}4$) substrates. Journal of Crystal Growth, 1999, 201-202, 226-231.	0.7	4
74	Nano-oxidation of Vanadium Thin Films using Atomic Force Microscopy. Journal of Materials Science Letters, 1998, 17, 1941-1943.	0.5	5
75	Low dimensional carrier confinement structure grown on patterned GaAs(111)A substrates by molecular beam epitaxy. Microelectronic Engineering, 1998, 43-44, 403-407.	1.1	0
76	Lateral-junction light emitting devices grown by molecular beam epitaxy on GaAs (311)A-oriented substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 94-98.	1.7	1
77	Oxide-confinement vertical-cavity surface-emitting lasers grown on GaAs(311)A substrates with dynamically stable polarisation. Electronics Letters, 1998, 34, 276.	0.5	14
78	A light-emitting device using a lateral junction grown by molecular beam epitaxy on GaAs (311)A-oriented substrates. Applied Physics Letters, 1998, 72, 818-820.	1.5	33
79	Spontaneous Formation of Nanostructures in $\text{In}_x\text{Ga}_{1-x}\text{As}$ Epilayers Grown by Molecular Beam Epitaxy on GaAs Non-(100)-oriented Substrates. Japanese Journal of Applied Physics, 1997, 36, 1948-1954.	0.8	17
80	The growth of (InGa)As quantum wells on GaAs(111)A, (211)A and (311)A substrates. Microelectronics Journal, 1997, 28, 1011-1018.	1.1	2
81	Piezoelectricity and carrier dynamics in $\text{In}_{0.2}\text{Ga}_{0.8}\text{As}$ /GaAs single quantum wells grown on (111)A-oriented GaAs ($n=1, 2, 3$). Microelectronics Journal, 1997, 28, 749-755.	1.1	1
82	MBE growth of AlGaAs/GaAs double- heterostructure light emitting diodes on GaAs(111)A and (211)A substrates using all-silicon doping. Microelectronics Journal, 1997, 28, 1019-1023.	1.1	4
83	MBE growth of lattice-matched and mismatched films on non-(001) GaAs substrates. Thin Solid Films, 1997, 306, 192-197.	0.8	2
84	An InGaAs-GaAs vertical-cavity surface-emitting laser grown on GaAs(311)A substrate having low threshold and stable polarization. IEEE Photonics Technology Letters, 1996, 8, 737-739.	1.3	67
85	AlGaAs/GaAs and InGaAs/GaAs quantum wells grown on GaAs (111)A substrates. Microelectronics Journal, 1996, 27, 411-421.	1.1	8
86	Rapid collapse of Wannier- Stark localization caused by space charge electric field screening in short-period superlattices. Journal of Applied Physics, 1996, 80, 5094-5105.	1.1	3
87	Electron drift reversal caused by remaining holes in semiconductor superlattices due to effective-mass filtering. Physical Review B, 1996, 53, R13283-R13286.	1.1	1
88	Carrier Dynamics in Piezoelectric Quantum Wells Grown on GaAs (111)A, (211)A and (311)A Studied by Time-Resolved Photoluminescence Spectroscopy. Japanese Journal of Applied Physics, 1996, 35, 1292-1298.	0.8	9
89	Growth and Characterization of Vertical-Cavity Surface-Emitting Lasers Grown on (311)A-Oriented GaAs Substrates by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1996, 35, 6102-6107.	0.8	22
90	Optical properties of a nanostructure spontaneously formed on GaAs (311)A-oriented substrates. Journal Physics D: Applied Physics, 1996, 29, 2221-2228.	1.3	18

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91	Strain relaxation in InGaAs/GaAs quantum wells grown on GaAs (111)A substrates. Journal of Crystal Growth, 1995, 150, 503-507.	0.7	2
92	Characterization of InGaAs/GaAs strained-layer quantum wells grown on (311)A GaAs substrates. Applied Physics Letters, 1995, 66, 93-95.	1.5	10
93	Influence of the Piezoelectric Effect on the Energy Levels of InGaAs/GaAs Strained Quantum Wells Grown on (311)A GaAs. Japanese Journal of Applied Physics, 1995, 34, L13-L16.	0.8	15
94	Quantum-Confined Stark Shift Due to Piezoelectric Effect in InGaAs/GaAs Quantum Wells Grown on (111)A GaAs. Japanese Journal of Applied Physics, 1995, 34, 1362-1366.	0.8	25
95	Growth by molecular-beam epitaxy and photoluminescence of InGaAs/GaAs quantum wells on GaAs (111)A substrates. Journal of Applied Physics, 1994, 76, 8037-8041.	1.1	15
96	In-situ RHEED observation on surface reactions in laser-triggered chemical beam epitaxy of GaP. Applied Surface Science, 1994, 79-80, 227-231.	3.1	3
97	In-situ reflection high-energy electron diffraction observation of laser-triggered GaP growth in chemical beam epitaxy. Journal of Crystal Growth, 1994, 136, 89-93.	0.7	0
98	Laser decomposition of surface adsorbed metalorganics in MOMBE growth of GaP. , 1994, , 163-166.		0
99	Atomic-Layer Control in GaP Growth by Laser-Triggered Chemical Beam Epitaxy. Japanese Journal of Applied Physics, 1993, 32, L335-L337.	0.8	5
100	Reflection high-energy electron diffraction observation of surface reaction triggered by pulsed laser irradiation during GaP growth in chemical beam epitaxy. Applied Physics Letters, 1993, 63, 2097-2099.	1.5	2
101	Model for reflection high-energy electron diffraction intensity recovery during GaP growth in laser-triggered chemical beam epitaxy. Applied Physics Letters, 1993, 63, 3601-3603.	1.5	0
102	Growth of polycrystalline CdIn ₂ S ₄ on US films. Journal of Materials Science Letters, 1993, 12, 553-554.	0.5	0
103	Effects of CdCl ₂ on the growth of CdTe on CdS films for solar cells by isothermal close-spaced vapour transport. Journal Physics D: Applied Physics, 1991, 24, 1886-1889.	1.3	5
104	Isothermal close-spaced vapour growth of CdTe for CdS/CdTe solar cells. Journal of Materials Science Letters, 1991, 10, 47-48.	0.5	0
105	Photoconductivity in stannic oxide films prepared by spray pyrolysis. Journal of Materials Science Letters, 1990, 9, 389-390.	0.5	11
106	High performance strained-layer InGaAs quantum well lasers grown on a (311)A GaAs substrate. , 0, , .		0
107	Piezoelectric effect in InGaAs/GaAs quantum wells grown on (111)A GaAs observed by photoluminescence spectroscopy. , 0, , .		0
108	Epitaxial growth and amphoteric doping on GaAs (n11)A-oriented substrates. , 0, , .		0

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109	Theoretical analysis of transient processes in lateral p-n junction photodiodes. , 0, , .		0
110	Longitudinal mode behavior of a lateral-junction edge-emitting laser diode. , 0, , .		0
111	Self-assembly of micro-stage using micro-origami technique on GaAs. , 0, , .		1
112	Observation of electronic band-structure modification in microtubed quantum well. , 0, , .		0
113	Influence of substrate orientation on self-assembled InAs/GaAs quantum dots for long wavelength emission grown by molecular beam epitaxy. , 0, , .		0
114	On the design and fabrication precision of Micro-Origami devices. , 0, , .		2
115	Si doped p- and n-type Al/sub x/Ga/sub 1-x/As epilayers for high density lateral-junction LED arrays on [311]A patterned substrate. , 0, , .		0
116	Generation of Ultrasonic Waves from an Optically Driven GaAs Thin Film. , 0, , .		0